

T-39-31

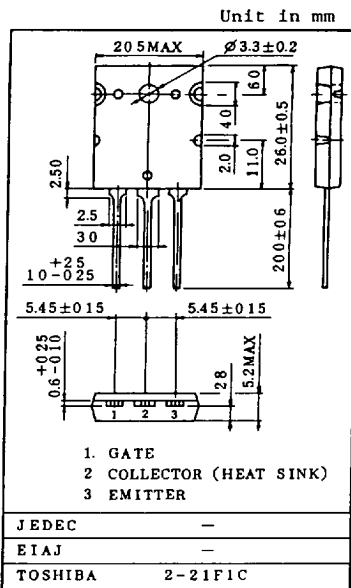
TOSHIBA (DISCRETE/OPTO)

HIGH POWER AMPLIFIER APPLICATION

- . High Breakdown Voltage : $V_{CES} = -250V$ (MIN.)
- . High Forward Transfer Admittance : $|Y_{fe}| = 10S$ (TYP.)
- . Complementary to GT20D101
- . Enhancement-Mode

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	-250	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	I_C	-20	A
Latch Up Current	I_L	-60	A
Collector Power Dissipation (Tc=25°C)	PC	180	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55-150	°C

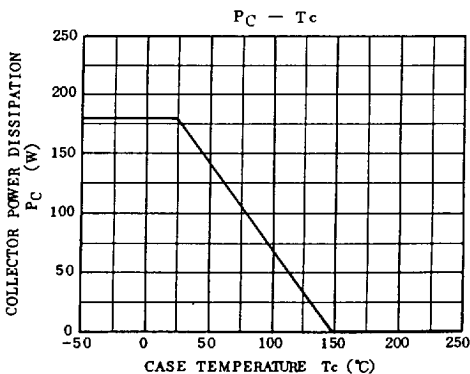
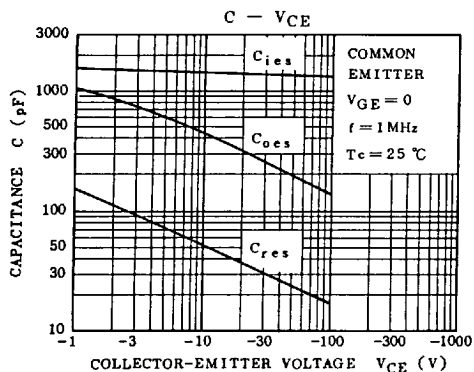
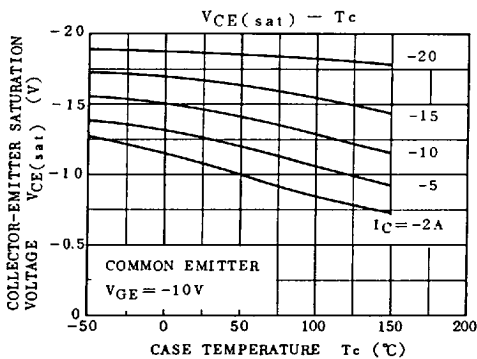
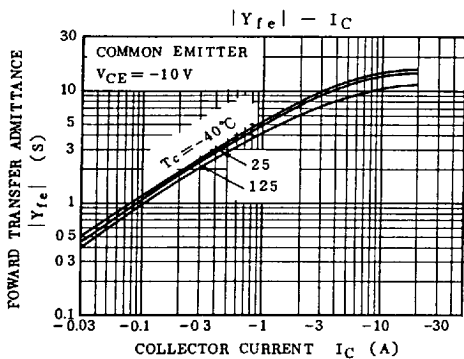
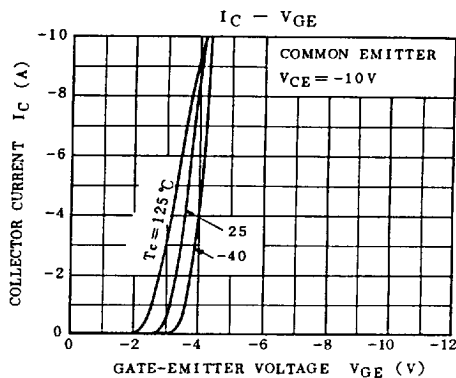
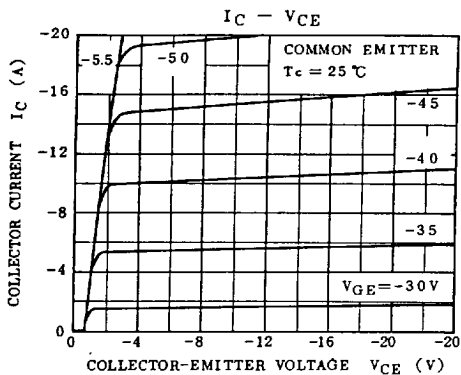


Weight : 9.75g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CES}	$V_{CE} = -250V, V_{GE} = 0$	-	-	-50	μA
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	-	-	± 0.5	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = -100\mu A, V_{GE} = 0$	-250	-	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -15A, V_{GE} = -10V$	-	-1.7	-3.0	V
Gate-Emitter Cut-off Voltage (Note)	$V_{GE(OFF)}$	$V_{CE} = -10V, I_C = -100mA$	-1.0	-	-3.6	V
Forward Transfer Admittance	$ Y_{fe} $	$V_{CE} = -10V, I_C = -1A$	-	3	-	S
	$ Y_{fe} $	$V_{CE} = -10V, I_C = -10A$	-	10	-	
Input Capacitance	C_{ies}	$V_{CE} = -10V, V_{GE} = 0, f = 1MHz$	-	1450	-	pF
Output Capacitance	C_{oes}	$V_{CE} = -10V, V_{GE} = 0, f = 1MHz$	-	450	-	pF
Reverse Transfer Capacitance	C_{res}	$V_{CE} = -10V, V_{GE} = 0, f = 1MHz$	-	50	-	pF

(Note) $V_{GE(OFF)}$ Classification O : -1.0~2.4 Y : -2.2~3.6



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GT20D201

